

Please amend the claims as follows:

A1 1. (Amended) An integrated semiconductor circuit device comprising a diode bridge circuit formed of a Schottky barrier diode and a periphery circuit formed of a MOS transistor which are formed on a single silicon substrate, wherein a Schottky barrier, which is a component of the Schottky barrier diode, is formed of a silicide layer, another silicide layer is formed on source/drain regions and a gate electrode, which are components of the MOS transistor, and both of the silicide layers are layers formed at the same time in self-alignment is made of a silicide layer.